

SEMiX452GAL126HDs



SEMiX® 2s

Trench IGBT Modules

SEMiX452GAL126HDs

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

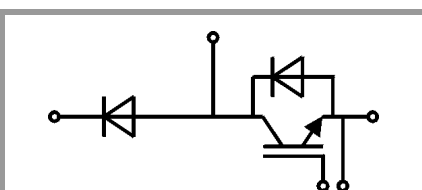
- Case temperatur limited to $T_C=125^{\circ}\text{C}$ max.
- Not for new design

Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^{\circ}\text{C}$	1200	V
I_C	$T_j = 150^{\circ}\text{C}$	$T_c = 25^{\circ}\text{C}$	455
		$T_c = 80^{\circ}\text{C}$	319
I_{Cnom}		300	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	600	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 20\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125^{\circ}\text{C}$	10
T_j		-40 ... 150	$^{\circ}\text{C}$
Inverse diode			
I_F	$T_j = 150^{\circ}\text{C}$	$T_c = 25^{\circ}\text{C}$	394
		$T_c = 80^{\circ}\text{C}$	272
I_{Fnom}		300	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	600	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^{\circ}, T_j = 25^{\circ}\text{C}$	1900	A
T_j		-40 ... 150	$^{\circ}\text{C}$
Freewheeling diode			
I_F	$T_j = 150^{\circ}\text{C}$	$T_c = 25^{\circ}\text{C}$	373
		$T_c = 80^{\circ}\text{C}$	258
I_{Fnom}		300	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	600	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^{\circ}, T_j = 25^{\circ}\text{C}$	1900	A
T_j		-40 ... 150	$^{\circ}\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^{\circ}\text{C}$	600	A
T_{stg}		-40 ... 125	$^{\circ}\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^{\circ}\text{C}$	1.7	2.10	V
		$T_j = 125^{\circ}\text{C}$	2.0	2.45	V
V_{CE0}	chipelevel	$T_j = 25^{\circ}\text{C}$	1	1.2	V
		$T_j = 125^{\circ}\text{C}$	0.9	1.1	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^{\circ}\text{C}$	2.3	3.0	$\text{m}\Omega$
		$T_j = 125^{\circ}\text{C}$	3.7	4.5	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 12\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^{\circ}\text{C}$		4.0	mA
		$T_j = 125^{\circ}\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	21.5		nF
C_{oes}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1.13		nF
C_{res}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.98		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		2400		nC
R_{Gint}	$T_j = 25^{\circ}\text{C}$		2.50		Ω



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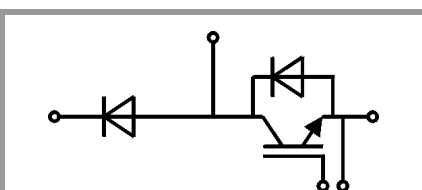
Typical Applications*

- AC inverter drives
- UPS
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Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C		280		ns
t _r	I _C = 300 A	T _j = 125 °C		65		ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C		35		mJ
t _{d(off)}	R _{G on} = 2 Ω	T _j = 125 °C		630		ns
t _f	R _{G off} = 2 Ω	T _j = 125 °C		130		ns
E _{off}		T _j = 125 °C		45		mJ
R _{th(j-c)}	per IGBT				0.083	K/W
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		1.6	1.80	V
	V _{GE} = 0 V chipelevel	T _j = 125 °C		1.6	1.8	V
V _{F0}	chipelevel	T _j = 25 °C	0.9	1	1.1	V
		T _j = 125 °C	0.7	0.8	0.9	V
r _F	chipelevel	T _j = 25 °C	1.7	2.0	2.3	mΩ
		T _j = 125 °C	2.3	2.7	3.0	mΩ
I _{RRM}	I _F = 300 A	T _j = 125 °C		375		A
Q _{rr}	di/dt _{off} = 6200 A/μs	T _j = 125 °C		75		μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C		33		mJ
	V _{CC} = 600 V	T _j = 125 °C				
R _{th(j-c)}	per diode				0.15	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		1.7	1.91	V
	V _{GE} = 0 V chipelevel	T _j = 125 °C		1.7	1.9	V
V _{F0}	chipelevel	T _j = 25 °C	0.9	1	1.1	V
		T _j = 125 °C	0.7	0.8	0.9	V
r _F	chipelevel	T _j = 25 °C	1.9	2.3	2.7	mΩ
		T _j = 125 °C	2.7	3.1	3.5	mΩ
I _{RRM}	I _F = 300 A	T _j = 125 °C		375		A
Q _{rr}	di/dt _{off} = 6200 A/μs	T _j = 125 °C		75		μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C		33		mJ
	V _{CC} = 600 V	T _j = 125 °C				
R _{th(j-c)}	per diode				0.15	K/W
Module						
L _{CE}				18		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.045		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w					250	g
Temperature Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R(T)=R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



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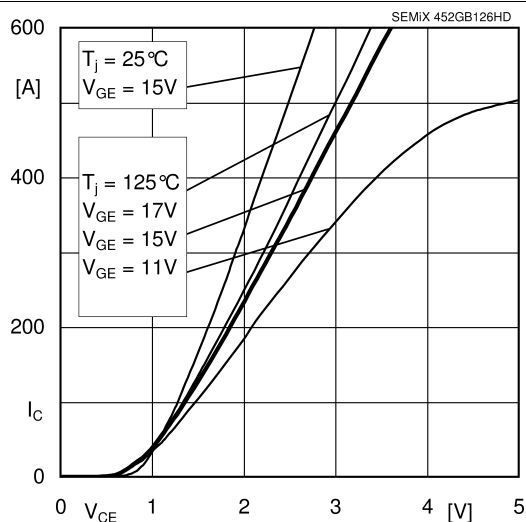


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_{E'}$

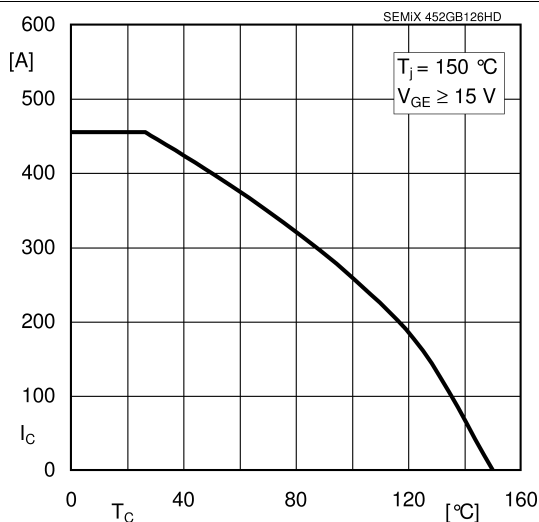


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

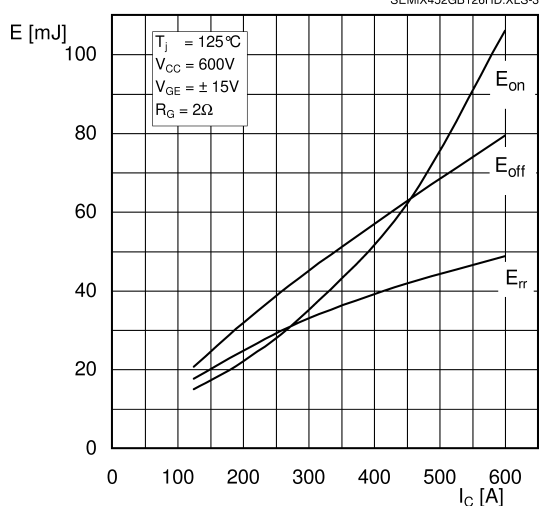


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

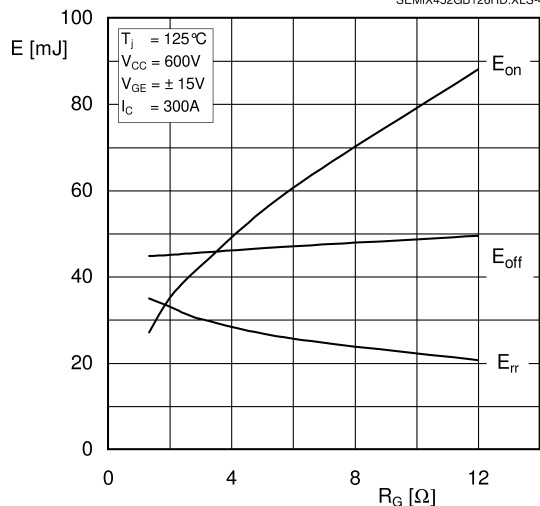


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

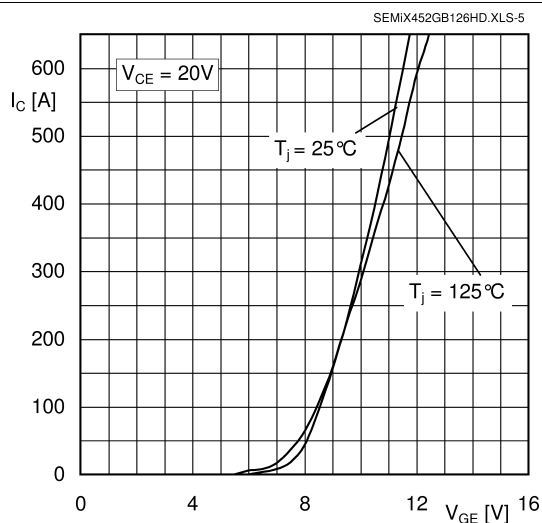


Fig. 5: Typ. transfer characteristic

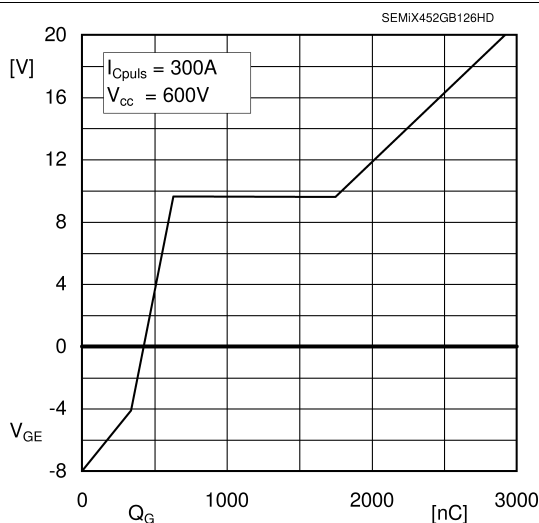
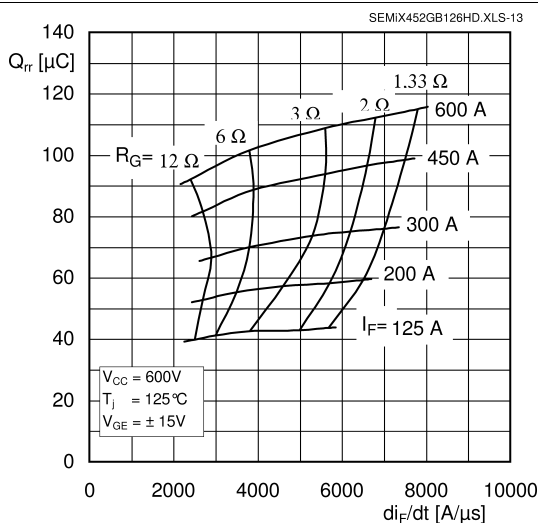
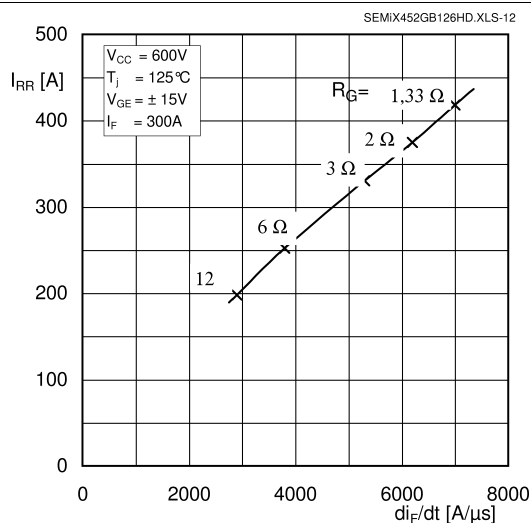
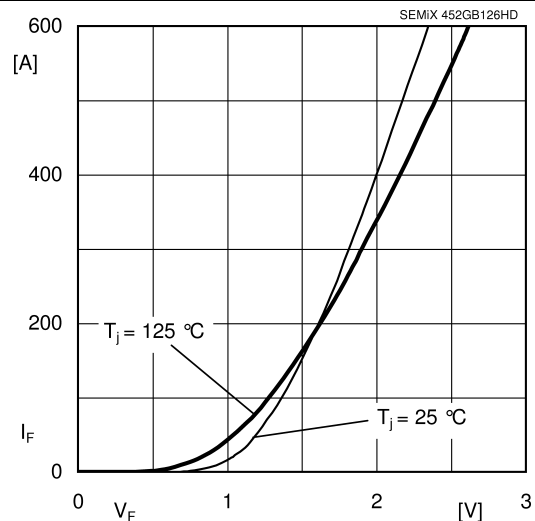
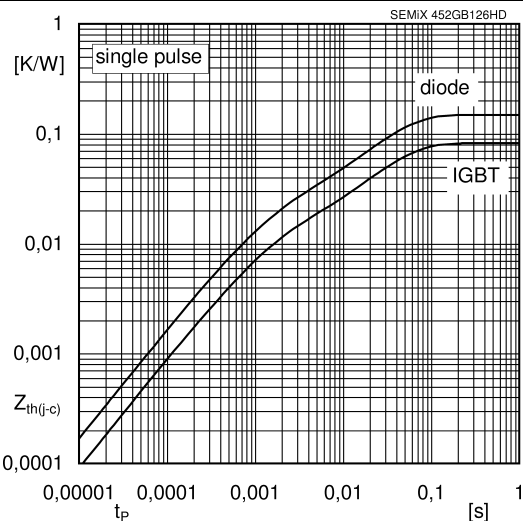
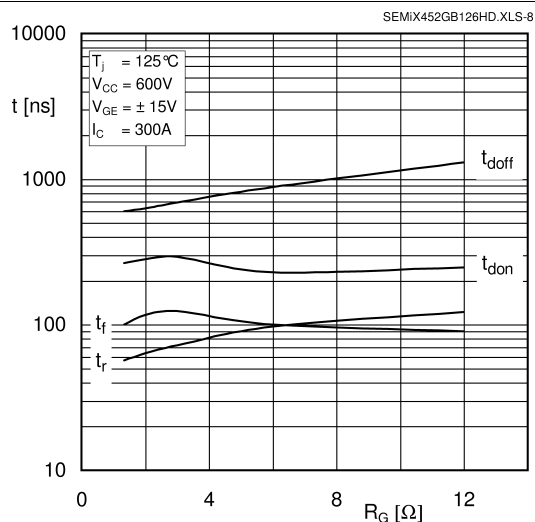
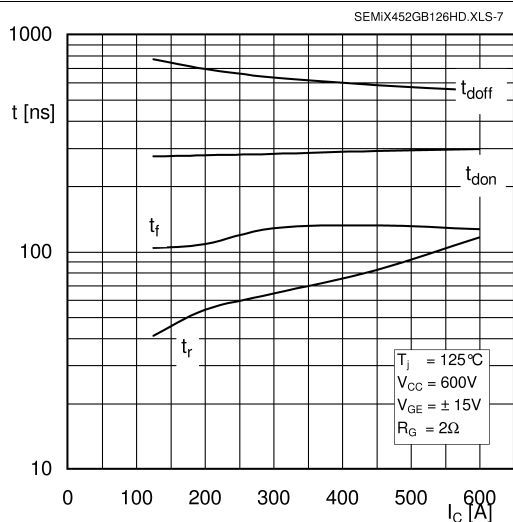
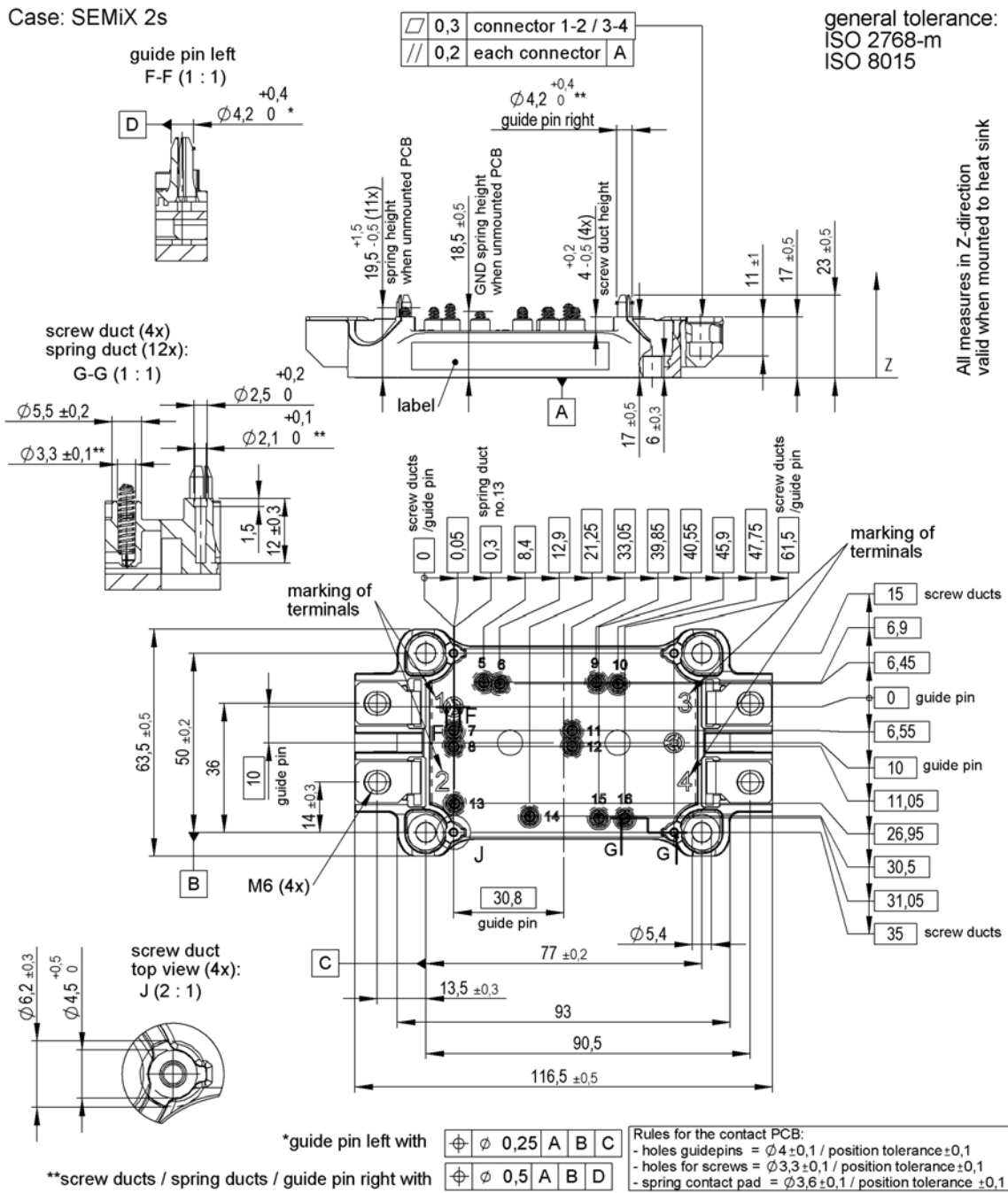


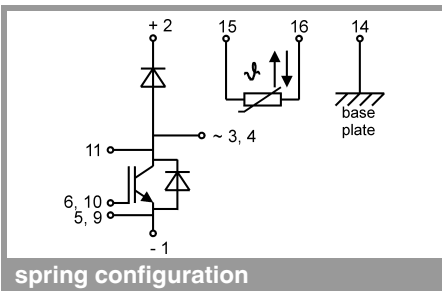
Fig. 6: Typ. gate charge characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.